

I claim:

1. A method for forming an interconnecting substrate, comprising
 - providing a support base,
 - disposing on said support base a decoupling capacitor, and
 - employing a deposition process to form an interconnect layer [having a pattern of circuit connections] over said decoupling capacitor, whereby an interconnecting substrate is formed having an embedded decoupling capacitor.
 2. A method according to claim 1, including forming electrical connections on a surface of said interconnect layer and extending into said interconnect layer, thereby allowing devices to be mounted on said surface of said interconnect layer.
 3. A method according to claim 1, wherein employing a deposition process to form an interconnect layer includes forming an interconnect layer having a power and a ground plane.
 4. A method according to claim 1, wherein employing a deposition process to form an interconnect layer includes forming an interconnect layer having a plurality of signal planes.
 5. A method according to claim 1, wherein disposing on said support base a decoupling capacitor includes disposing on said support base a plurality of decoupling capacitors.

6. A method according to claim 1, wherein disposing on said support base a decoupling capacitor includes disposing on said support base a plurality of decoupling capacitors having a common ground plane.
- 5 7. A method according to claim 1, wherein disposing on said support base a decoupling capacitor includes forming a capacitor on said support base.
- 10 8. A method according to claim 1, including disposing on said support base a terminating resistor.
- 15 9. A method according to claim 1, including disposing a device on a surface of said interconnect layer at locations selected to reduce an interconnect length between said device and said decoupling capacitor.
- 20 10. A method according to claim 1, including wire bonding devices to a surface of said interconnect layer.
11. A method according to claim 1, including flip-chip mounting devices to a surface of said interconnect layer.
- 25 12. A device for interconnecting a plurality of circuit devices, comprising
a support base having a first surface,
a decoupling capacitor mounted on said first surface, and
an interconnect layer having a pattern of circuit connections and being
formed over and surrounding said decoupling capacitor, whereby said decoupling capacitor is embedded within said interconnect layer.

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13. A device according to claim 12, wherein said interconnect layer includes a power plane and a ground plane, and wherein said decoupling capacitor connects in parallel between said power and ground planes.
- 5 14. A device according to claim 12, further comprising a plurality of decoupling capacitors mounted on said first surface.
- 10 15. A device according to claim 12, further comprising a resistor mounted to said first surface.
- 15 16. A device according to claim 12, wherein said support base comprises a silicon containing substrate.
- 20 17. A device according to claim 12, wherein said decoupling capacitor comprises a silicon containing dielectric material.
- 25 18. A device according to claim 12, wherein said interconnecting layer comprises a plurality of aluminum containing conductive paths.
19. A device according to claim 12 wherein said interconnecting layer comprises a plurality of copper containing conductive paths.
20. A device according to claim 12, wherein said decoupling capacitor comprises a die.